

Is Now Part of



ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at <u>www.onsemi.com</u>

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized applications, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an equif prese



Motion-SPM [™]

May 2016

FSB50825AB

Smart Power Module (SPM[®])

Features

- 250V R_{DS(on)}=0.45Ω max) 3-phase FRFET inverter including high voltage integrated circuit (HVIC)
- 3 divided negative dc-link terminals for inverter current sensing applications
- HVIC for gate driving and undervoltage protection
- Optimized for low electromagnetic interference
- Isolation voltage rating of 1500Vrms for 1min.
- · HVIC temperature sensing
- · Embedded bootstrap diode in the package
- · RoHS compliant

Applications

· Three-phase inverter driver for small power ac motor drives

General Description

FSB50825AB is a tiny smart power module (SPM[®]) based on FRFET technology as a compact inverter solution for small power motor drive applications such as fan motors and water suppliers. It is composed of 6 fast-recovery MOSFET (FRFET), and 3 half-bridge HVICs for FRFET gate driving. FSB50825AB provides low electromagnetic interference (EMI) characteristics with optimized switching speed. Moreover, since it employs FRFET as a power switch, it has much better ruggedness and larger safe operation area (SOA) than that of an IGBT-based power module or one-chip solution. The package is optimized for the thermal performance and compactness for the use in the built-in motor application and any other application where the assembly space is concerned. FSB50825AB is the best solution for the compact inverter providing the energy efficiency, compactness, and low electromagnetic interference.



Absolute Maximum Ratings

Inverter Part (Each FRFET Unless Otherwise Specified)

Symbol	Parameter	Conditions	Rating	Units
V _{PN}	DC Link Input Voltage, Drain-source Voltage of each FRFET		250	V
*I _{D25}	Each FRFET Drain Current, Continuous	$T_{\rm C} = 25^{\circ}{\rm C}$	3.6	A
*I _{D80}	Each FRFET Drain Current, Continuous	$T_{\rm C} = 80^{\circ}{\rm C}$	2.7	A
*I _{DP}	Each FRFET Drain Current, Peak	T _C = 25°C, PW < 100μs	9	A
*I _{DRMS}	Each FRFET Drain Current, Rms	T _C = 80°C, F _{PWM} < 20KHz	1.9	A _{rms}
*P _D	Maximum Power Dissipation	T_{C} = 25°C, For Each FRFET	14.2	W

Control Part (Each HVIC Unless Otherwise Specified)

Symbol	Parameter	Conditions	Rating	Units
V _{CC}	Control Supply Voltage	Applied between $V_{\mbox{\scriptsize CC}}$ and COM	20	V
V _{BS}	High-side Bias Voltage	Applied between V_{B} and V_{S}	20	V
V _{IN}	Input Signal Voltage	Applied between IN and COM	$-0.3 \sim V_{CC} + 0.3$	V

Bootstrap Diode Part (Each Bootstrap diode Unless Otherwise Specified)

Symbol	Parameter	Parameter Conditions		Units
V _{RRMB}	Maixmum Repetitive Reverse Voltage		250	V
* I _{FB}	Forward Current	T _C = 25°C	0.5	A
* I _{FPB}	Forward Current (Peak)	T_{C} = 25°C, Under 1ms Pulse Width	1.5	А

Thermal Resistance

Symbol	Parameter	Conditions	Rating	Units
R _{θJC}	Junction to Case Thermal Resistance	Each FRFET under inverter operat- ing condition (Note 1)	8.8	°C/W

Total System

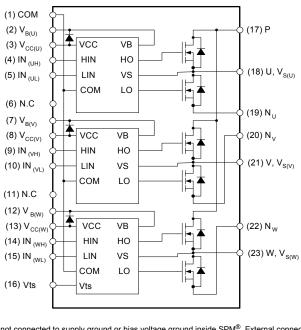
Symbol	Parameter	Conditions	Rating	Units
TJ	Operating Junction Temperature		-40 ~ 150	°C
T _{STG}	Storage Temperature		-40 ~ 125	°C
V _{ISO}	Isolation Voltage	60Hz, Sinusoidal, 1 minute, Con- nection pins to heatsink	1500	V _{rms}

Note:

1. For the measurement point of case temperature $T_{C^{\!\!}}$ please refer to Figure 4.

2. Marking "* " is calculation value or design factor.

Pin Number	Pin Name	Pin Description
1	СОМ	IC Common Supply Ground
2	V _{B(U)}	Bias Voltage for U Phase High Side FRFET Driving
3	V _{CC(U)}	Bias Voltage for U Phase IC and Low Side FRFET Driving
4	IN _(UH)	Signal Input for U Phase High-side
5	IN _(UL)	Signal Input for U Phase Low-side
6	N.C	N.C
7	V _{B(V)}	Bias Voltage for V Phase High Side FRFET Driving
8	V _{CC(V)}	Bias Voltage for V Phase IC and Low Side FRFET Driving
9	IN _(VH)	Signal Input for V Phase High-side
10	IN _(VL)	Signal Input for V Phase Low-side
11	N.C	N.C
12	V _{B(W)}	Bias Voltage for W Phase High Side FRFET Driving
13	V _{CC(W)}	Bias Voltage for W Phase IC and Low Side FRFET Driving
14	IN _(WH)	Signal Input for W Phase High-side
15	IN _(WL)	Signal Input for W Phase Low-side
16	V _{ts}	Output for HVIC temperature sensing
17	Р	Positive DC-Link Input
18	U, V _{S(U)}	Output for U Phase & Bias Voltage Ground for High Side FRFET Driving
19	NU	Negative DC-Link Input for U Phase
20	N _V	Negative DC–Link Input for V Phase
21	V, V _{S(V)}	Output for V Phase & Bias Voltage Ground for High Side FRFET Driving
22	N _W	Negative DC–Link Input for W Phase
23	W, V _{S(W)}	Output for W Phase & Bias Voltage Ground for High Side FRFET Driving





Note:

Electrical Characteristics (T_J = 25°C, V_{CC} = V_{BS} =15V Unless Otherwise Specified)

Inverter Part (Each FRFET Unless Otherwise Specified)

Symbol	Parameter	Conditions	Min	Тур	Max	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{IN} = 0V, I _D = 1mA (Note 1)	250	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{IN} = 0V, V _{DS} = 250V		-	1	mA
R _{DS(on)}	Static Drain-Source On-Resistance	V _{CC} = V _{BS} = 15V, V _{IN} = 5V, I _D = 2A	-	0.33	0.45	Ω
V _{SD}	Drain-Source Diode Forward Voltage	V _{CC} = V _{BS} = 15V, V _{IN} = 0V, I _D = -2A	-	-	1.2	V
t _{ON}			-	950	-	ns
t _{OFF}		V_{PN} = 150V, V_{CC} = V_{BS} = 15V, I_D = 2A V_{IN} = 0V \leftarrow 5V, Inductive load L=3mH High- and low-side FRFET switching	-	520	-	ns
t _{rr}	Switching Times		-	140	-	ns
E _{ON}		(Note 2)	-	100	-	μJ
E _{OFF}				10	-	μJ
RBSOA	Reverse-bias Safe Oper- ating Area	$ V_{PN} = 200V, V_{CC} = V_{BS} = 15V, I_D = I_{DP}, V_{DS} = BV_{DSS}, \\ T_J = 150^{\circ}C \\ High- and low-side FRFET switching (Note 3) $	Full Square			

Control Part (Each HVIC Unless Otherwise Specified)

Symbol	Parameter		Conditions	Min	Тур	Max	Units
I _{QCC}	Quiescent V _{CC} Current	V _{CC} =15V, V _{IN} =0V	Applied between $V_{\mbox{\scriptsize CC}}$ and COM	-	-	200	μA
I _{QBS}	Quiescent V _{BS} Current	V _{BS} =15V, V _{IN} =0V	Applied between $V_{B(U)}$ -U, $V_{B(V)}$ -V, $V_{B(W)}$ -W	-	-	100	μΑ
UV _{CCD}	Low-side Undervoltage	V _{CC} Undervoltage I	V _{CC} Undervoltage Protection Detection Level		8.0	9.4	V
UV _{CCR}	Protection (Figure 8) V _{CC} Undervoltage Protection Reset Level		8.0	8.9	9.8	V	
UV _{BSD}	High-side Undervoltage	V _{BS} Undervoltage F	V _{BS} Undervoltage Protection Detection Level		8.0	9.4	V
UV _{BSR}	Protection (Figure 9)	V _{BS} Undervoltage Protection Reset Level		8.0	8.9	9.8	V
V _{ts}	HVIC Temperature sens- ing voltage output	V _{CC} =15V, T _{HVIC} =25°C(Note 4)		600	790	980	mV
V _{IH}	ON Threshold Voltage	Logic High Level	Applied between IN and COM	-	-	2.9	V
V _{IL}	OFF Threshold Voltage	Logic Low Level	Applied between IN and COM	0.8	-	-	V

Bootstrap Diode Part (Each Bootstrap diode Unless Otherwise Specified)

Symbol	Parameter	Conditions	Min	Тур	Max	Units
V _{FB}	Forward Voltage	I _F = 0.1A, T _C = 25°C(Note 5)	-	2.5	-	V
t _{rrB}	Reverse Recovery Time	I _F = 0.1A, T _C = 25°C	-	80	-	ns

Note:

1. BV_{DSS} is the absolute maximum voltage rating between drain and source terminal of each FRFET inside SPM[®]. V_{PN} should be sufficiently less than this value considering the effect of the stray inductance so that V_{DS} should not exceed BV_{DSS} in any case.

t_{ON} and t_{OFF} include the propagation delay time of the internal drive IC. Listed values are measured at the laboratory test condition, and they can be different according to the field applications due to the effect of different printed circuit boards and wirings. Please see Figure 6 for the switching time definition with the switching test circuit of Figure 7.
The peak current and voltage of each FRFET during the switching operation should be included in the safe operating area (SOA). Please see Figure 7 for the RBSOA test circuit of the result of the re

cuit that is same as the switching test circuit. 4. V_{ts} is only for sensing temperature of module and cannot shutdown MOSFETs automatically.

5. Built in bootstrap diode includes around 15 Ω resistance characteristic. Please refer to Figure 2.

Recommended Operating Condition

Symbol	Parameter	Conditions	Value			Units
Symbol	Falailletei	Conditions	Min.	Тур.	Max.	Units
V _{PN}	Supply Voltage	Applied between P and N	-	150	200	V
V _{CC}	Control Supply Voltage	Applied between V _{CC} and COM	12	13.5	15	V
V _{BS}	High-side Bias Voltage	Applied between V_{B} and V_{S}	12	13.5	15	V
V _{IN(ON)}	Input ON Threshold Voltage	Applied between IN and COM	3.0	-	V _{CC}	V
V _{IN(OFF)}	Input OFF Threshold Voltage		0	-	0.6	V
t _{dead}	Blanking Time for Preventing Arm-short	V_{CC} =V _{BS} =12 ~ 15V, T _J \leq 150°C	1.0	-	-	μs
f _{PWM}	PWM Switching Frequency	$T_{J} \leq 150^{\circ}C$	-	15	-	kHz

Package Marking & Ordering Information

Device Marking	Device	Package	Reel Size	Packing Type	Quantity
FSB50825AB	FSB50825AB	SPM23DD-21L	-	-	15

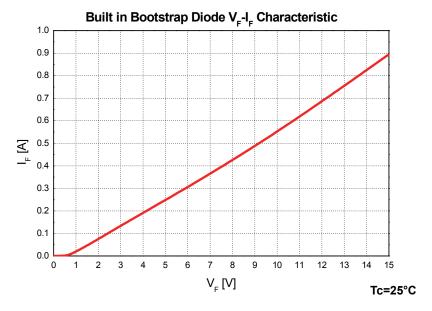
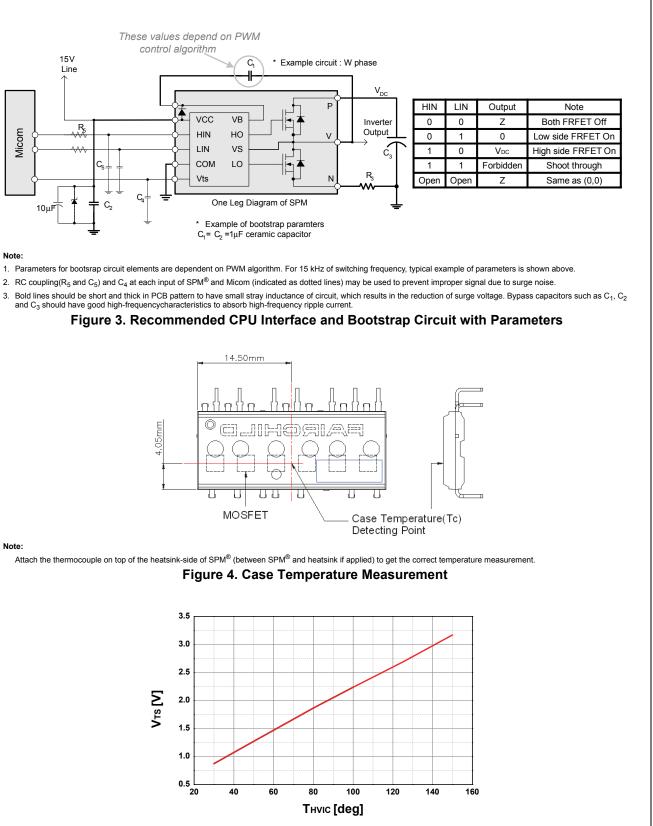


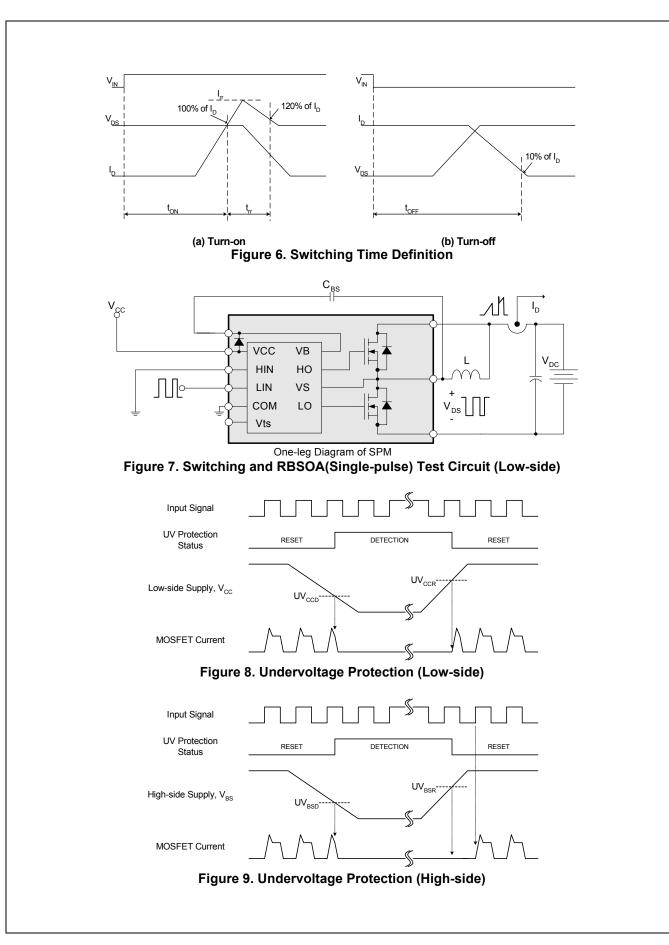
Figure 2. Built in Bootstrap Diode Characteristics(typ.)

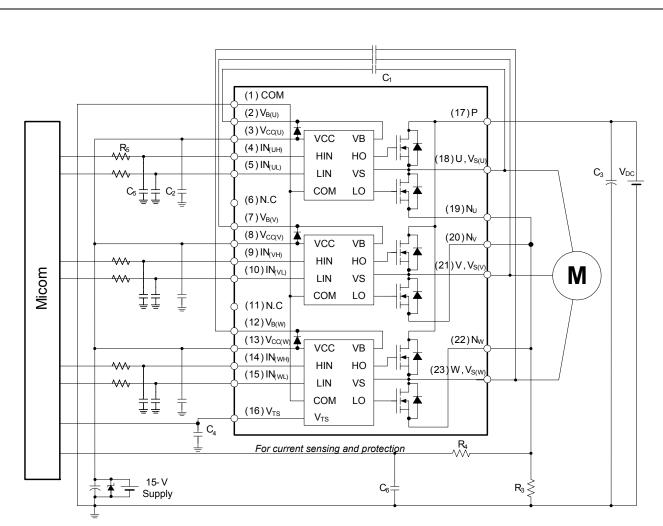




FSB50825AB Smart Power Module (SPM®)

FSB50825AB Smart Power Module (SPM®)





Note:

1. About pin position, refer to Figure 2.

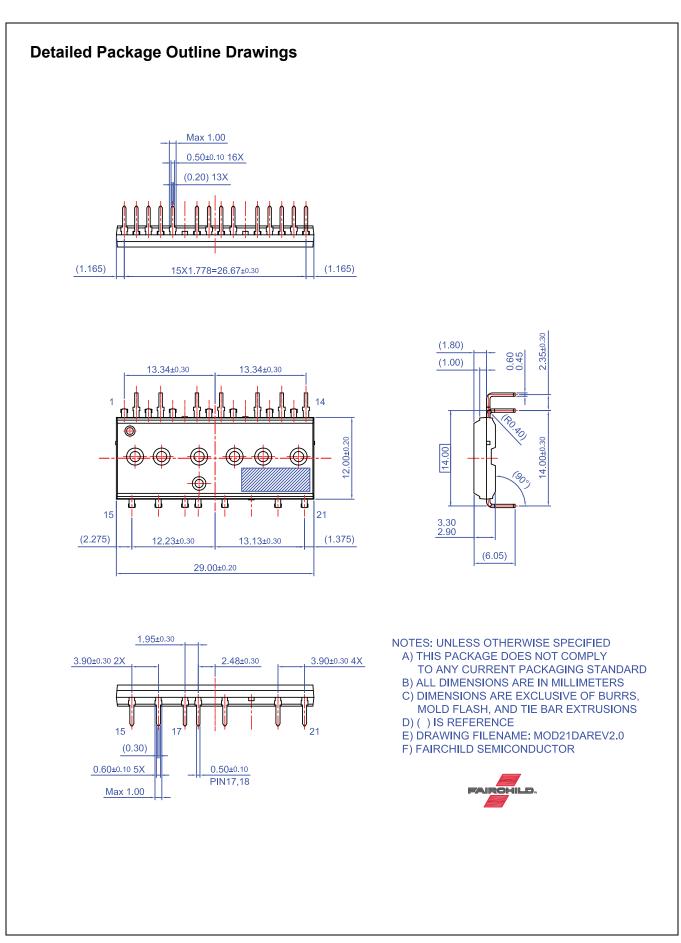
2. RC coupling (R₅ and C₅, R₄ and C₆) and C₄ at each input of SPM[®] and Micom are useful to prevent improper input signal caused by surge noise.

3. The voltage drop across R₃ affects the low side switching performance and the bootstrap characteristics since it is placed between COM and the source terminal of the low side MOSFET. For this reason, the voltage drop across R₃ should be less than 1V in the steady-state.

4. Ground wires and output terminals, should be thick and short in order to avoid surge voltage and malfunction of HVIC.

5. All the filter capacitors should be connected close to SPM®, and they should have good characteristics for rejecting high-frequency ripple current.

Figure 10. Example of Application Circuit



FSB50825AB Smart Power Module (SPM®)



Rev. 177

© Fairchild Semiconductor Corporation

www.fairchildsemi.com

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent-Marking.pdf</u>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor haves against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly ori indirectly, any claim of personal injury or death

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center Phone: 81-3-5817-1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

© Semiconductor Components Industries, LLC

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

onsemi: FSB50825AB